

Substitute form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT JUL 02 2004

(use as many sheets as necessary)

Sheet A1 of A3

Complete if Known

Application Number 10/758,871

Filing Date January 16, 2004

First Named Inventor Sheppard

Group Art Unit 2812

Examiner Name Tom Thomas Geyer, S.

Attorney Docket Number 5308-291

U.S. PATENTS AND PATENT PUBLICATIONS					
Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
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Examiner Signature *SBG* Date Considered 12-8-05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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			Filing Date	January 16, 2004	
			First Named Inventor	Sheppard	
			Group Art Unit	2811 2812	
			Examiner Name	Tom Thomas GEYER	
Sheet	A2	of	A3	Attorney Docket Number	5308-291

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		Office	Number	Kind Code (if known)			
SBG	-50-	EP	0 563 847	A2	Matsushita Electric Industrial Co., Ltd.	10-06-1993	

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Examiner Signature		Date Considered	1-12-06
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